

- GENERAL PURPOSE SILICON DIODES
- ALL JUNCTIONS COMPLETELY PROTECTED WITH SILICON DIOXIDE
- COMPATIBLE WITH ALL WIRE BONDING AND DIE ATTACH TECHNIQUES EXCEPT SOLDER REFLOW

CD483B  
 CD485B  
 CD486B  
 CD645  
 AND  
 CD5194 thru CD5196

### MAXIMUM RATINGS

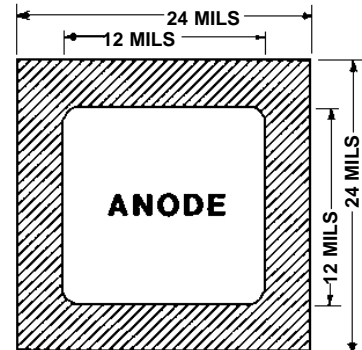
Operating Temperature: -65°C to +175°C  
 Storage Temperature: -65°C to +175°C

ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified

TYPE	$V_{RM}$	$V_{RWM}$	$I_O$	$I_O$	$I_{FSM}$
	$V_{(pk)}$	$V_{(pk)}$	mA	$T_A=+150^\circ C$ mA	$t_p = 1/120 S$ $T_A=25^\circ C$ A
CD483B	80	70	200	50	2
CD485B	180	180	200	50	2
CD486B	250	225	200	50	2
CD645	270	225	400	150	5
CD5194	80	70	200	50	2
CD5195	180	180	200	50	2
CD5196	250	225	200	50	2

TYPE	$V_F(1)$	$I_{R1}$ at $V_{RWM}$	$I_{R2}$ at $V_{RM}$	$I_{R3}$ at $V_{RWM}$	CAP @ $V_R$ =4V pF
	V dc	nA dc	$\mu A$	$\mu A$ dc	
CD483B	0.8 - 1.0	25	100	5	-
CD485B	0.8 - 1.0	25	100	5	-
CD486B	0.8 - 1.0	25	100	5	-
CD645	0.8 - 1.0	50	50	25	2.0
CD5194	0.8 - 1.0	25	100	5	-
CD5195	0.8 - 1.0	25	100	5	-
CD5196	0.8 - 1.0	25	100	5	-

NOTE 1 AT 100mA (pulsed) except for CD645  
 which is at 400mA (pulsed)



### DESIGN DATA

#### METALLIZATION:

Top: (Anode) .....Al  
 Back: (Cathode).....Au

AL THICKNESS .....25,000 Å Min

GOLD THICKNESS .....4,000 Å Min

CHIP THICKNESS .....10 Mils

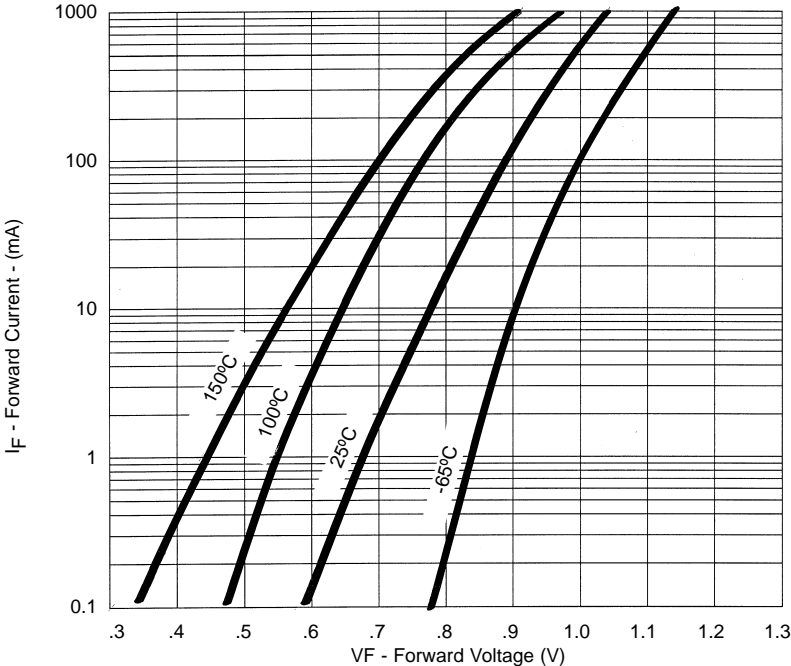
TOLERANCES: ALL  
 Dimensions  $\pm 2$  mils



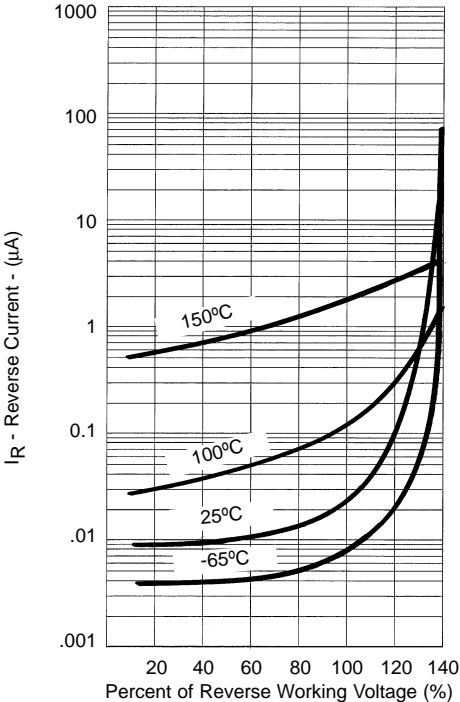
**COMPENSATED DEVICES INCORPORATED**

22 COREY STREET, MELROSE, MASSACHUSETTS 02176  
 PHONE (781) 665-1071 FAX (781) 665-7379  
 WEBSITE: <http://www.cdi-diodes.com> E-mail: [mail@cdi-diodes.com](mailto:mail@cdi-diodes.com)

# CD483B, CD485B, CD486B, CD645, CD5194 thru CD5196



**FIGURE 2**  
Typical Forward Current vs Forward Voltage



**NOTE :** All temperatures shown on graphs are junction temperatures

**FIGURE 3**  
Typical Reverse Current vs Reverse Voltage